

AlGaInP Ultra Bright Red LED Lamp

OPE5364UR

The **OPE5364UR** is AlGaInP ultra bright light emitting diode that is designed for ultra brightness and excellent reliability. This device is optimized for efficiency at peak wavelength 639nm.

This device is packaged T13/4 plastic package and has medium beam angle with lensed package and cup frame.

FEATURES

- Ultra brightness
- Peak wavelength : 639nm
- Medium beam angle
- Excellent reliability
- Available for pulse operating

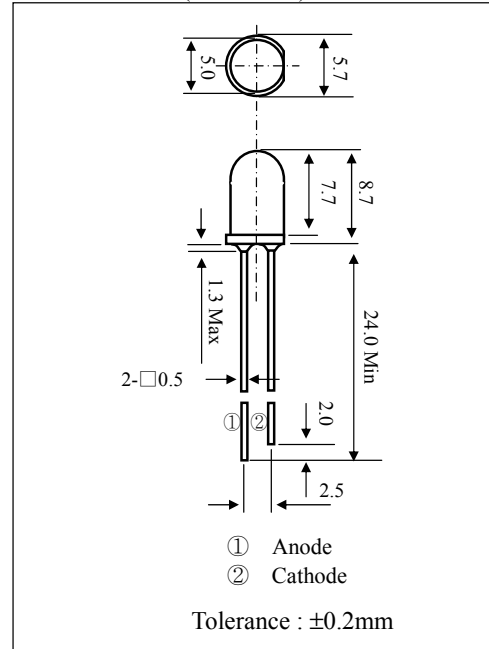
APPLICATIONS

- Pixel cluster
- LED Dot Matrix
- Traffic signal
- Display signboard

STORAGE

- Condition : 5°C~35°C,R.H.60%
- Terms : within 3 months from production date
- Remark : Once the package is opened, the products should be used within a day. Otherwise, it should be keeping in a damp proof box with desiccants.

DIMENSIONS (Unit : mm)



* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
Power dissipation	P_D	40	mW
Forward current	I_F	30	mA
Pulse forward current ^{*1}	I_{FP}	50	mA
Reverse voltage	V_R	4	V
Operating temp.	Topr.	-25~+85	°C
Soldering temp. ^{*2}	Tsol.	260.	°C

^{*1}.Duty ratio = 1/100, pulse width=0.1ms.

^{*2}.Lead soldering temperature (2mm from case for 5sec.).

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Luminous intensity	I_V	$I_F=20mA$				mcd
Peak emission wavelength	λ_p	$I_F=20mA$		639		nm
Spectral bandwidth	$\Delta\lambda$	$I_F=20mA$		20		nm
Forward voltage	V_F	$I_F=20mA$		2.0	2.4	V
Reverse current	I_R	$V_R=4V$			100	μA
Half angle	$\Delta\theta$	$I_F=20mA$		±15		deg.

